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Total No. of Questions : 4]		SEAT IV.	
PB	298	[6270]-87 [Total No. of Page	es :1
B.E. (E&TC) (Insem)			
NANO ELECTRONICS			
	(2	2019 Pattern) (Semester-VIII) (Elective-VI) (404192B)	
Time: 1 Hour]			:30
Instr		ns to the candidates:	
	1)	Answers Q.1 or Q.2, Q.3 or Q.4.	
	<i>2)</i>	Neat diagrams must be drawn wherever necessary.	
	3)	Figures to the right indicate full marks.	
	4)	Assume suitable data, if necessary.	
Q 1)	a)	What are different tools used for measuring nanostructures? Expl	lain
2)	,	principle & working of scanning Tunneling Microscope.	[7]
	b) \	Explain in detail the fundamental science behind nanotechnology.	[8]
	0)	Explain in detail the fandamental series genine hanceening og j.	[v]
		OR O	
Q 2)	a)	Describe the different tools used to make nanostructures.	[7]
	b)	Discuss the advantages & limitations of silicon material.	[8]
	0)	Discuss the advantage see infractions of smooth material.	
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Q3)	a)	Describe scanning probe instrument with neat diagram.	[5]
	b)	List different nano crystal non-volatile memories. Explain any one.	[5]
	,		
	c)	Draw & explain functioning of AFM.	[5]
		OR OR	

What are different lithography techniques? Explain any one. **Q4)** a) [5] Explain different novel dielectric materials for future transistors. b) [5] Write short notes on: Nano CMOS devices **[5]** c)

